

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

ECH8420 — General-Purpose Switching Device Applications

Features

- ON-resistance Rps(on)1=5.2m Ω (typ.)
- · 1.8V drive.
- · Halogen free compliance.
- · Protection diode in

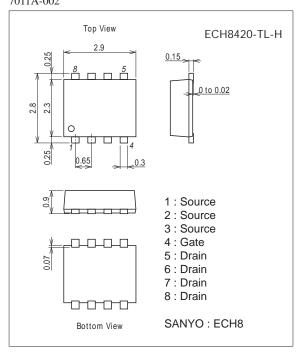
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		20	V
Gate-to-Source Voltage	V _{GSS}		±12	V
Drain Current (DC)	ID		14	А
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	50	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² ×0.8mm)	1.6	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

unit : mm (typ) 7011A-002

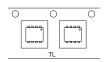


Product & Package Information

Package : ECH8JEITA, JEDEC : -

• Minimum Packing Quantity : 3,000 pcs./reel

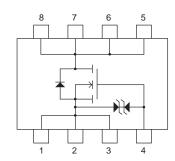
Packing Type: TL



Marking



Electrical Connection

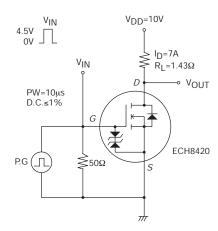


http://semicon.sanyo.com/en/network

Electrical Characteristics at Ta=25°C

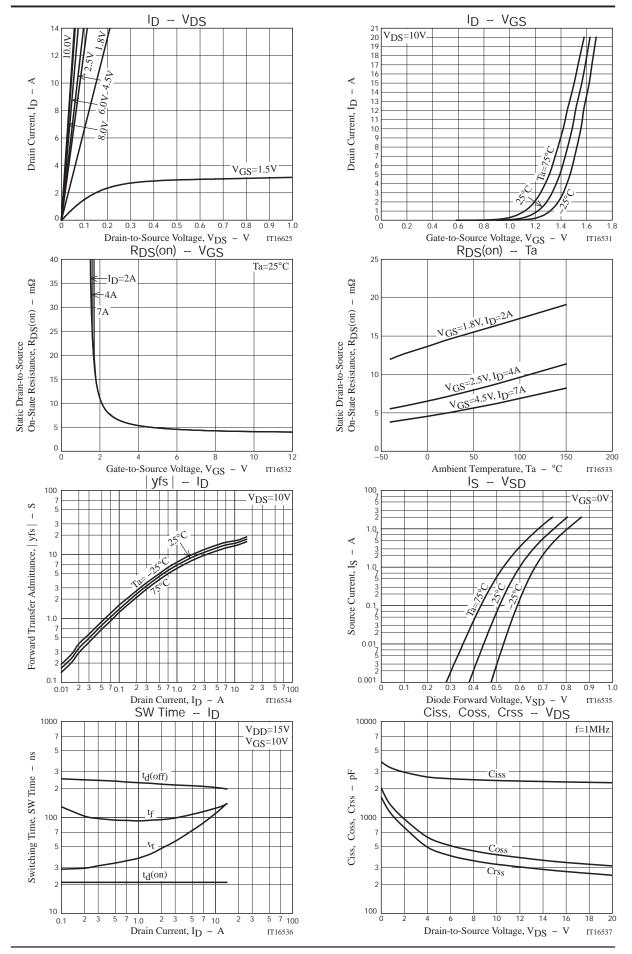
Doromotor	Complete	0 89	Ratings			1.114	
Parameter	Symbol	Conditions	min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	20			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0V			1	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	0.4		1.3	V	
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =7A		14.5		S	
	R _{DS} (on)1	I _D =7A, V _G S=4.5V		5.2	6.8	mΩ	
Static Drain-to-Source On-State Resistance	R _{DS} (on)2	I _D =4A, V _{GS} =2.5V		8	11.5	mΩ	
	RDS(on)3	I _D =2A, V _G S=1.8V		15	22.5	mΩ	
Input Capacitance	Ciss			2430		pF	
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		410		pF	
Reverse Transfer Capacitance	Crss			330		pF	
Turn-ON Delay Time	t _d (on)			21		ns	
Rise Time	tr	Can amonified Took Circuit		88		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		210		ns	
Fall Time	tf			115		ns	
Total Gate Charge	Qg			29		nC	
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =4.5V, I _D =14A		4.8		nC	
Gate-to-Drain "Miller" Charge	Qgd]		8.7		nC	
Diode Forward Voltage	V _{SD}	I _S =14A, V _{GS} =0V		0.75	1.2	V	

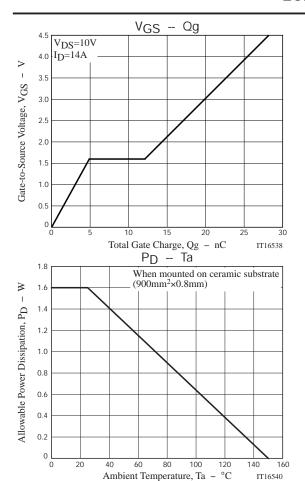
Switching Time Test Circuit

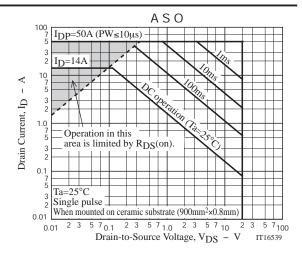


Ordering Information

Device	Device Package		memo	
ECH8420-TL-H	CH8420-TL-H ECH8		Pb Free and Halogen Free	





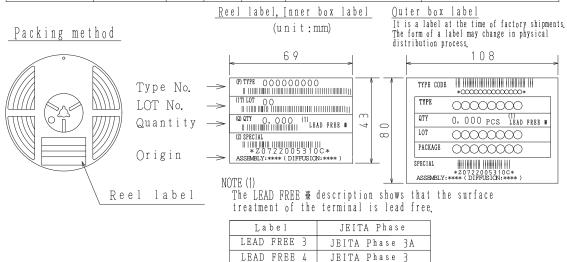


Embossed Taping Specification

ECH8420-TL-H

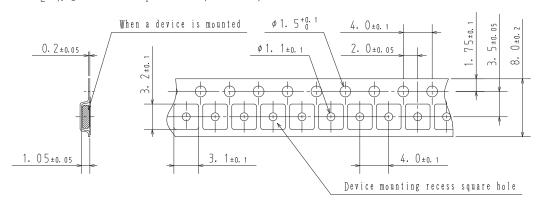
1. Packing Format

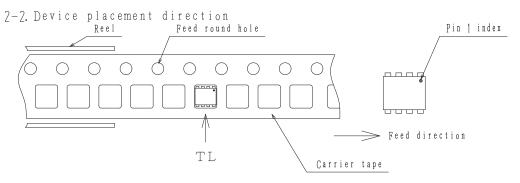
Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing	format
	Туре	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
ECH8	СРН6	3, 000	15, 000	90,000	5 reels contained	6 inner boxes contained
						Dimensions:mm (external)
					183×72×185	440×195×210



2. Taping configuration

7-1. Carrier tape size (unit:mm)

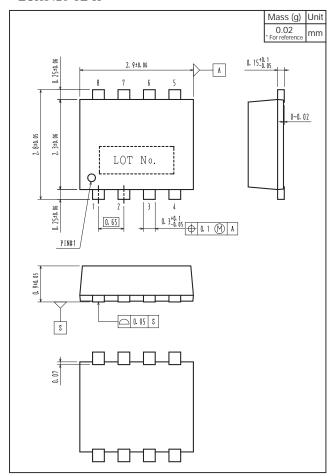




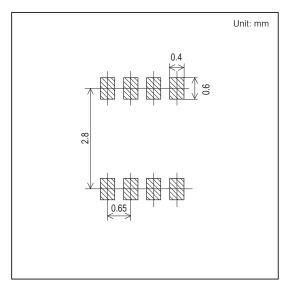
Those with pin 1 index on the feed hole side · · · · · TL

Outline Drawing

ECH8420-TL-H



Land Pattern Example



Note on usage: Since the ECH8420 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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